

21L02
276-2501

1024-BIT STATIC RANDOM ACCESS MEMORY

GENERAL DESCRIPTION

The 21L02 is a 1024-bit random access memory fabricated with high-density, high-reliability, N-channel, silicon-gate technology. For ease of use, the device operates from a single power supply, is directly compatible with TTL and DTL, and requires no clocks or refreshing because of static operation.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

FEATURES

- 1024 Word by 1 Bit Organization
- Access Time = 450 nA or less
- Low Power Dissipation—150mW Typical
- Static Operation
- Single +5-Volt Supply
- Direct TTL/DTL Compatibility
- Three-State Output
- Chip Enable for Memory Expansion
- Cost Effective Data Storage

RECOMMENDED DC OPERATING CONDITIONS

(Referenced to V_{SS})

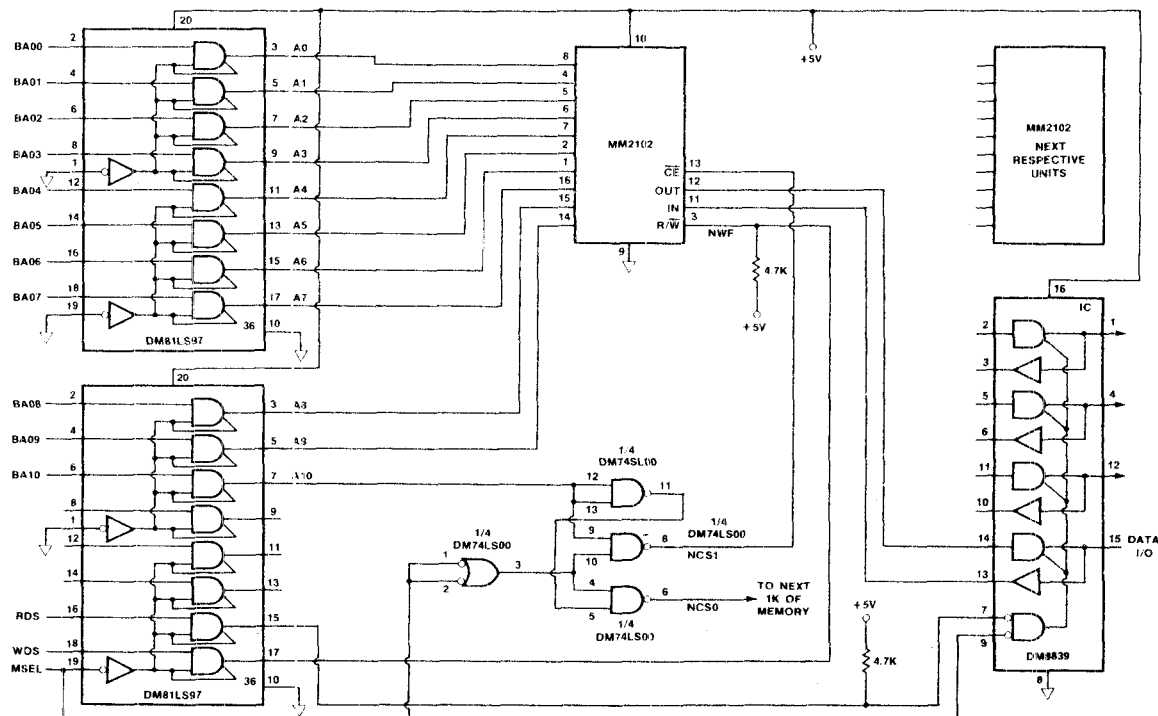
Supply Voltage.....	4.75 - 5.25 Vdc (MIN-MAX)
Input Low Voltage.....	-0.3 - 0.65 Vdc (MIN-MAX)
Input High Voltage.....	2.2 - 5.25 Vdc (MIN-MAX)

ABSOLUTE MAXIMUM RATINGS

(Referenced to V_{SS})

Supply Voltage.....	-0.3 to plus 7.0 Vdc
Input Voltage.....	-0.3 to plus 7.0 Vdc
Operating Temperature.....	0°C to plus 70°C
Storage Temperature Range.....	-55°C to plus 150°C

LOGIC DIAGRAM



PIN CONNECTION

